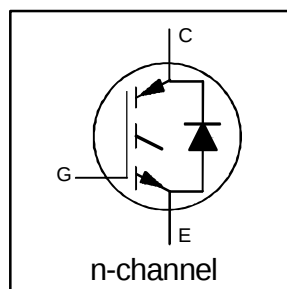


**INSULATED GATE BIPOLAR TRANSISTOR
WITH ULTRAFAST SOFT RECOVERY**

Fast CoPack IGBT

**DIODE
Features**

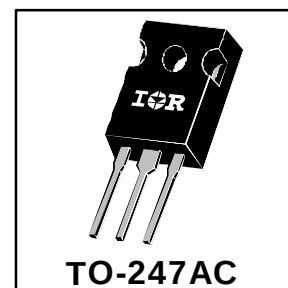
- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for medium operating frequency (1 to 10kHz) See Fig. 1 for Current vs. Frequency curve



$V_{CES} = 600V$
$V_{CE(sat)} \leq 2.0V$
@ $V_{GE} = 15V, I_C = 27A$

Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, motor control, UPS and power supply applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	49	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	27	
I_{CM}	Pulsed Collector Current ①	200	
I_{LM}	Clamped Inductive Load Current ②	200	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	15	
I_{FM}	Diode Maximum Forward Current	200	V
V_{GE}	Gate-to-Emitter Voltage	± 20	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	160	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	65	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	0.77	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	1.7	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temp. Coeff. of Breakdown Voltage	—	0.70	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	$I_C = 27A$
		—	2.2	—		$I_C = 49A$
		—	1.9	—		$I_C = 27A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temp. Coeff. of Threshold Voltage	—	-12	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ④	9.2	12	—	S	$V_{CE} = 100V, I_C = 27A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	3500		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.3	1.7	V	$I_C = 15A$
		—	1.2	1.6		$I_C = 15A, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	59	80	nC	$I_C = 27A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	8.6	10		$V_{CC} = 400V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	25	42		See Fig. 8
$t_{d(on)}$	Turn-On Delay Time	—	71	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	76	—		$I_C = 27A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	320	480		$V_{GE} = 15V, R_G = 10\Omega$
t_f	Fall Time	—	210	320		Energy losses include "tail" and diode reverse recovery.
E_{on}	Turn-On Switching Loss	—	1.3	—	mJ	See Fig. 9, 10, 11, 18
E_{off}	Turn-Off Switching Loss	—	3.2	—		
E_{ts}	Total Switching Loss	—	4.5	6.8		
$t_{d(on)}$	Turn-On Delay Time	—	70	—	ns	$T_J = 150^\circ\text{C}$, See Fig. 9, 10, 11, 18
t_r	Rise Time	—	73	—		$I_C = 27A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	540	—		$V_{GE} = 15V, R_G = 10\Omega$
t_f	Fall Time	—	480	—		Energy losses include "tail" and diode reverse recovery.
E_{ts}	Total Switching Loss	—	7.8	—	mJ	
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	1500	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	190	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	20	—		$f = 1.0MHz$
t_{rr}	Diode Reverse Recovery Time	—	42	60	ns	$T_J = 25^\circ\text{C}$ See Fig. 14
		—	74	120		$T_J = 125^\circ\text{C}$
I_{rr}	Diode Peak Reverse Recovery Current	—	4.0	6.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15
		—	6.5	10		$T_J = 125^\circ\text{C}$
Q_{rr}	Diode Reverse Recovery Charge	—	80	180	nC	$T_J = 25^\circ\text{C}$ See Fig. 16
		—	220	600		$T_J = 125^\circ\text{C}$
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	188	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17
		—	160	—		$T_J = 125^\circ\text{C}$

Notes:

① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature. (See fig. 20)

② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=10\Omega$, (See fig. 19)

③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.

④ Pulse width $5.0\mu s$, single shot.

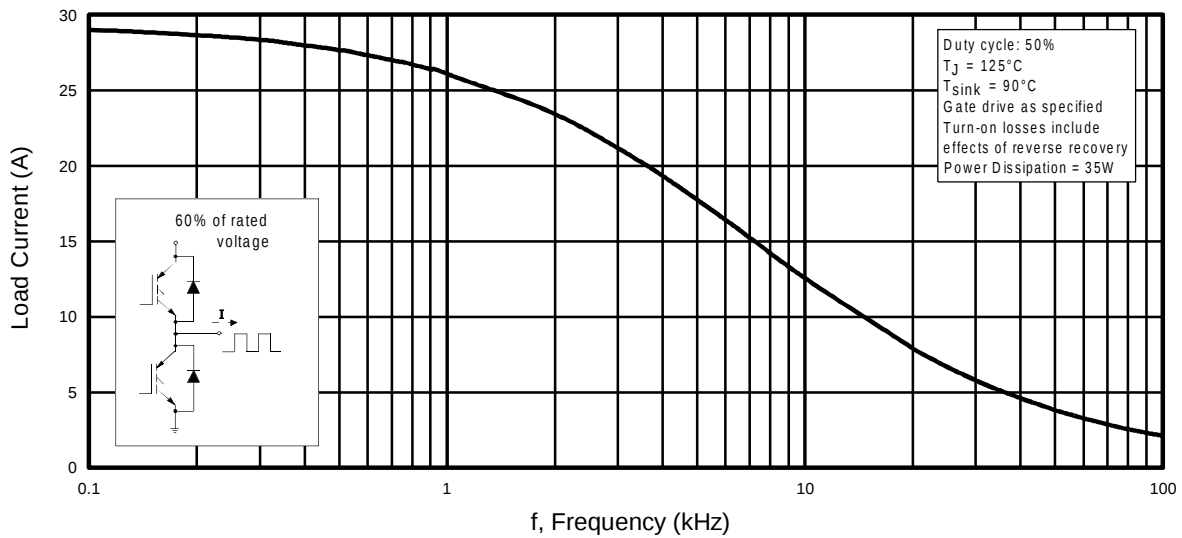


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

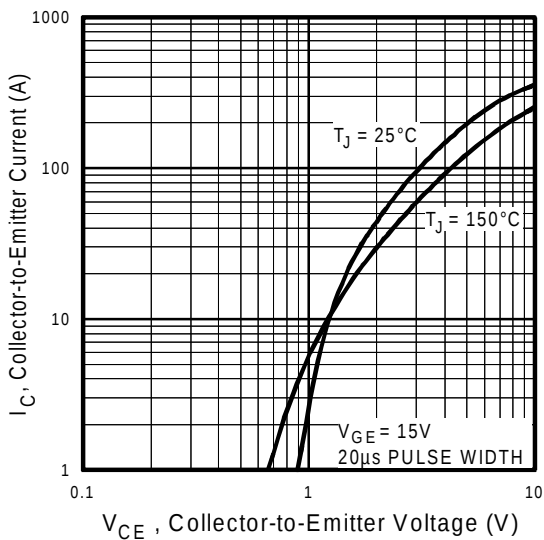


Fig. 2 - Typical Output Characteristics

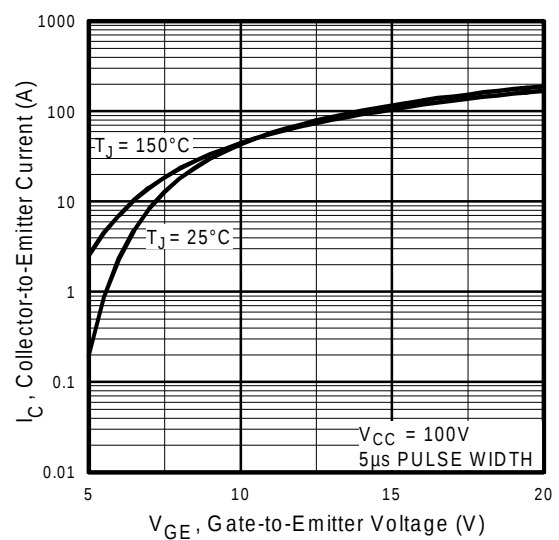


Fig. 3 - Typical Transfer Characteristics

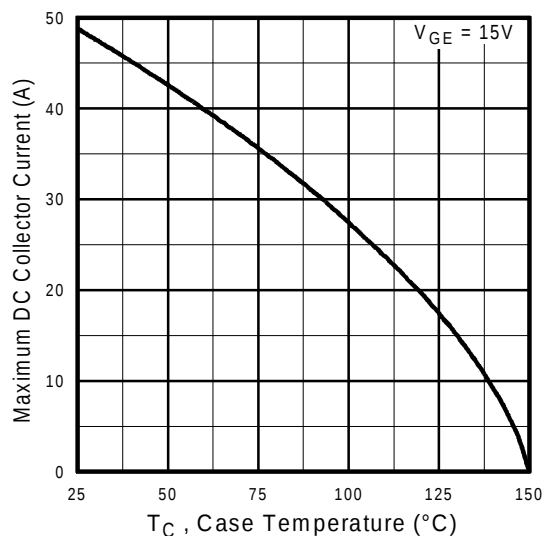


Fig. 4 - Maximum Collector Current vs. Case Temperature

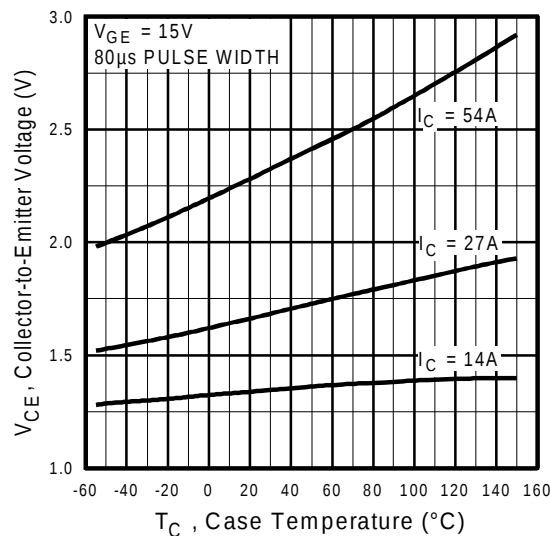


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

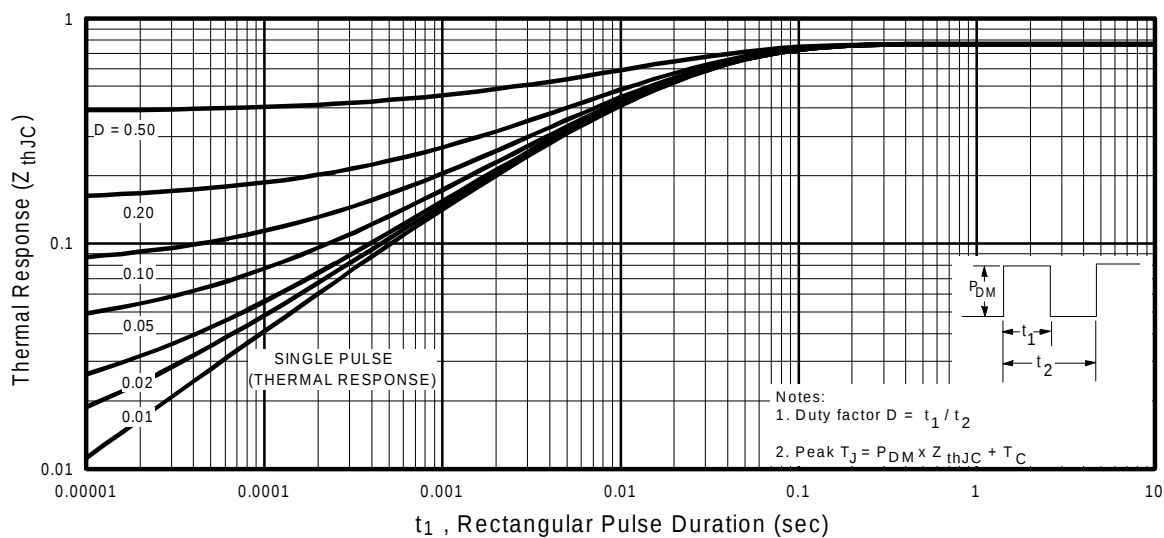


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

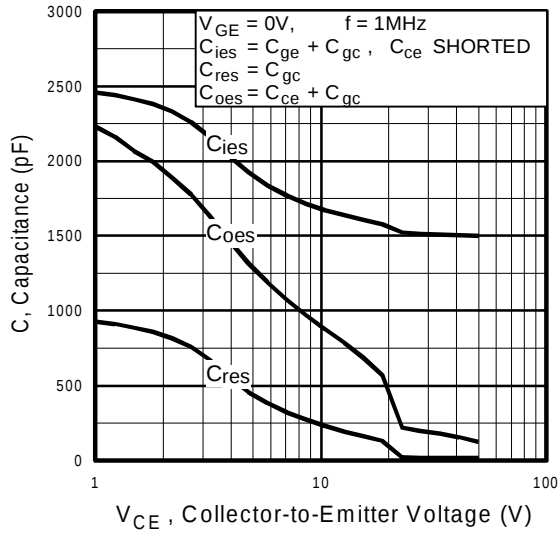


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

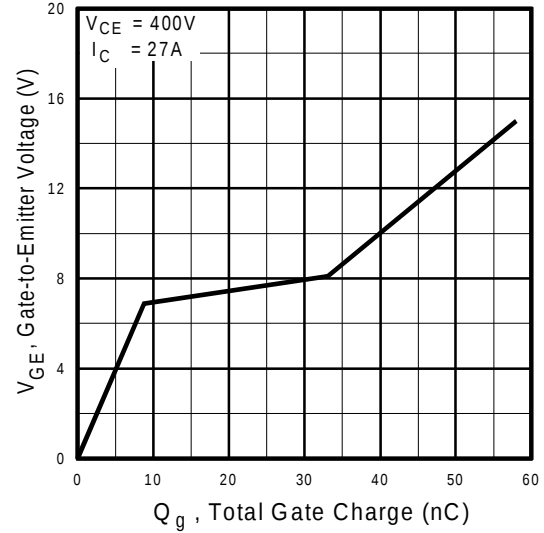


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

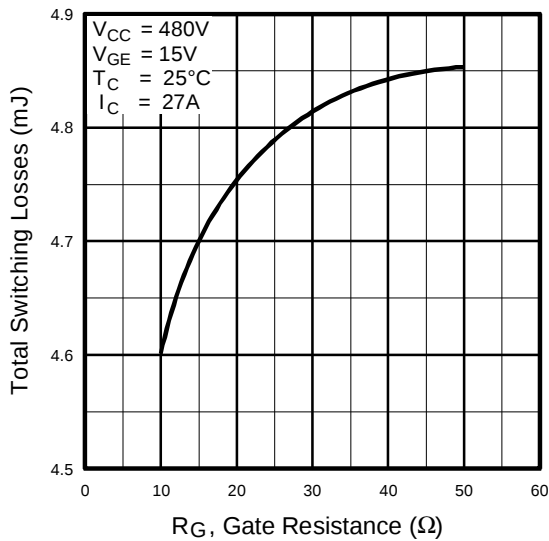


Fig. 9 - Typical Switching Losses vs. Gate Resistance

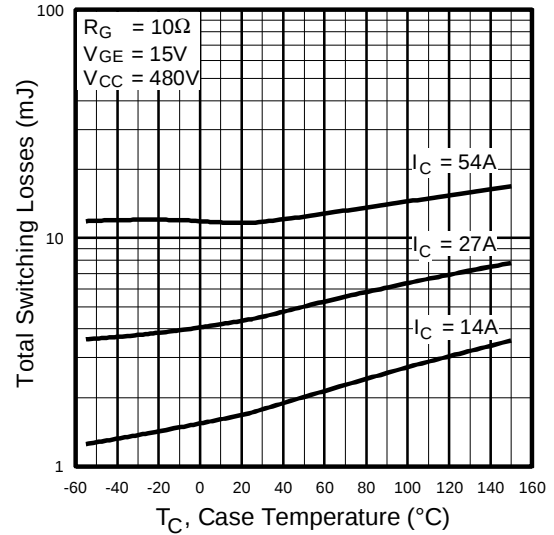


Fig. 10 - Typical Switching Losses vs. Case Temperature

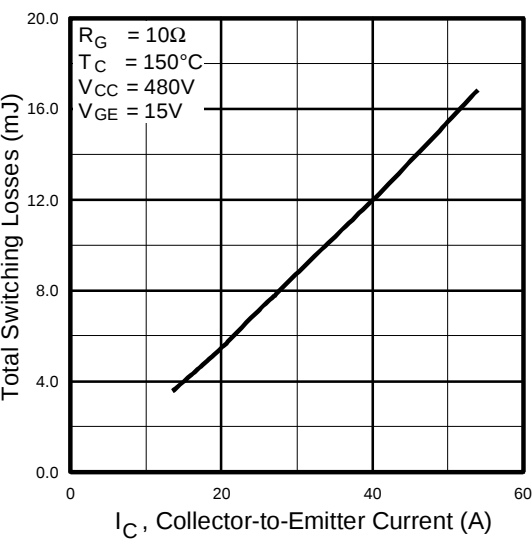


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

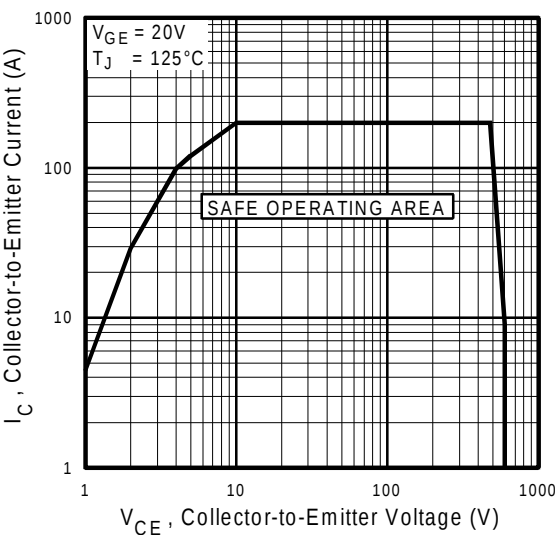


Fig. 12 - Turn-Off SOA

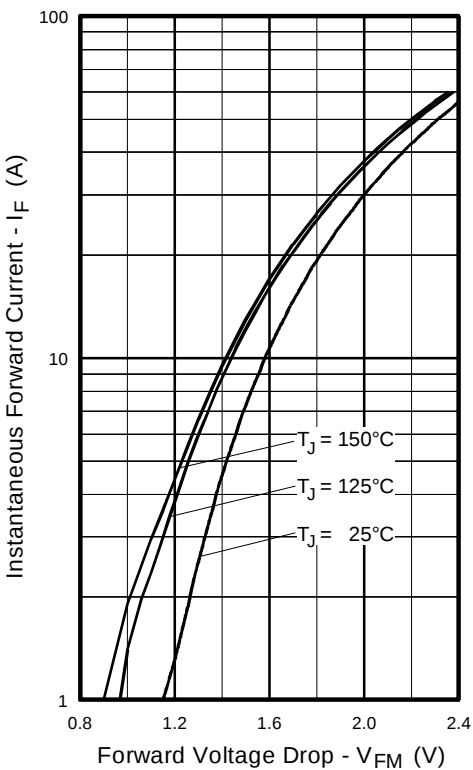


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

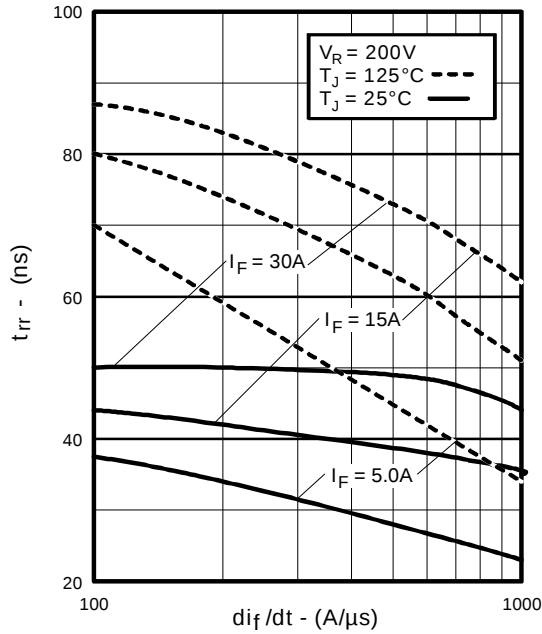


Fig. 14 - Typical Reverse Recovery vs. di/dt

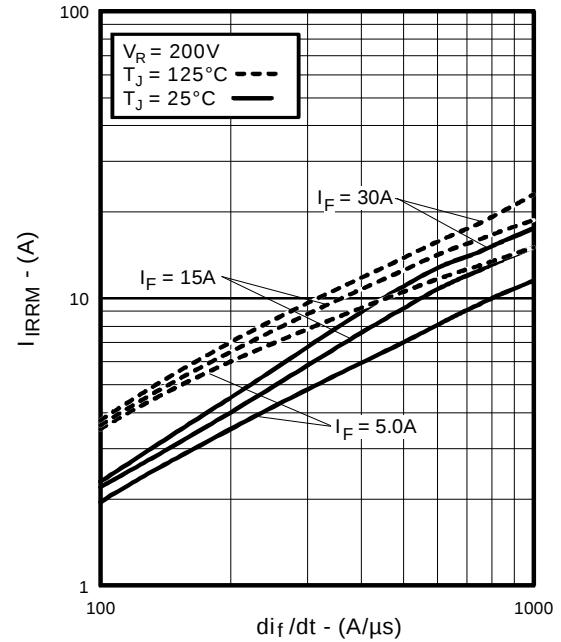


Fig. 15 - Typical Recovery Current vs. di/dt

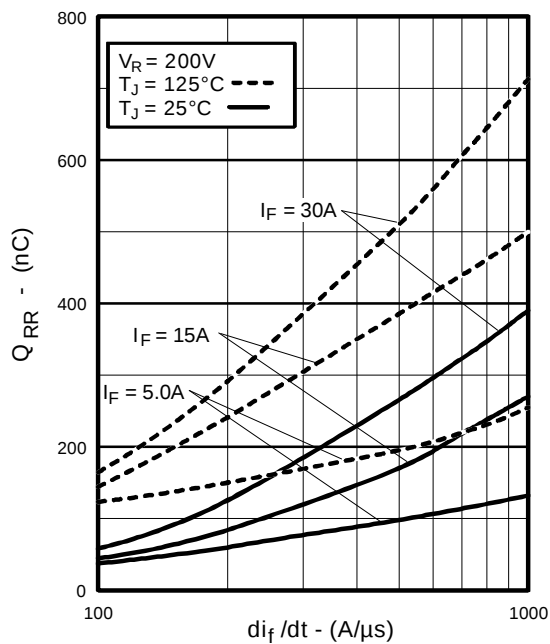


Fig. 16 - Typical Stored Charge vs. di/dt

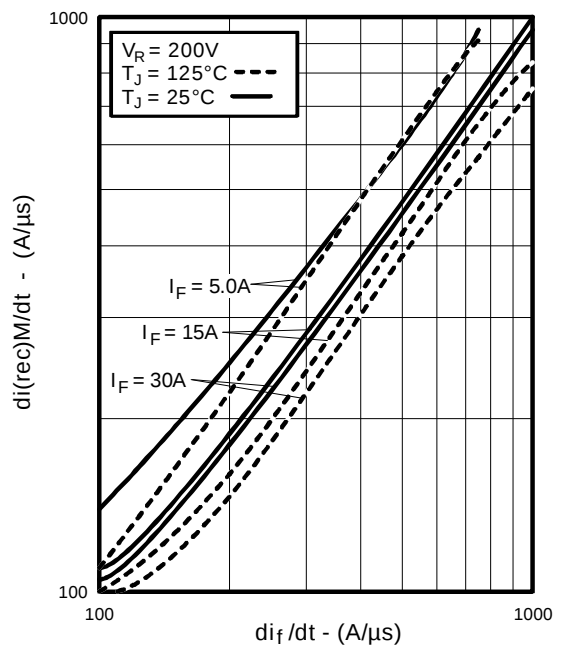


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di/dt

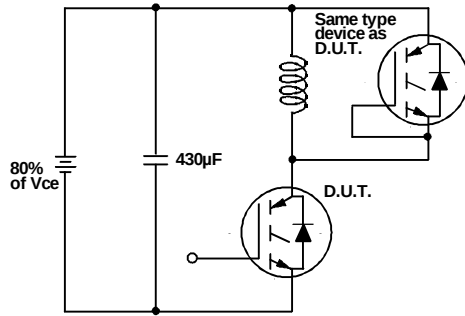


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

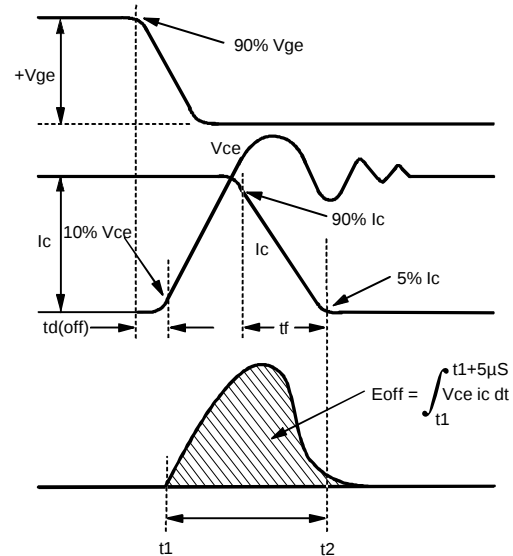


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

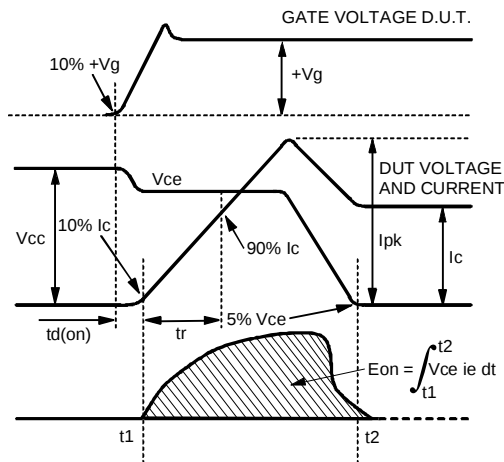


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

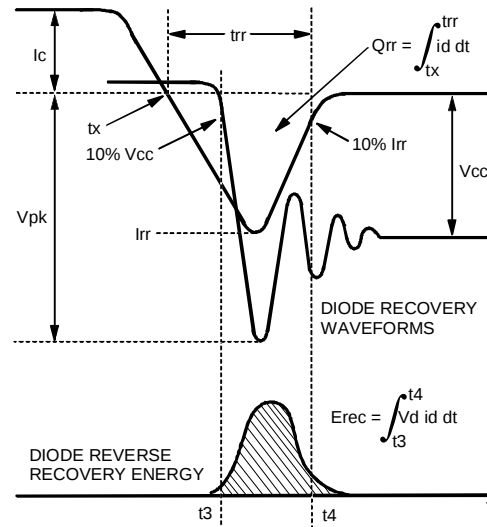


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

Refer to **Section D** for the following:
Appendix D: Section D - page D-6

Fig. 18e - Macro Waveforms for Test Circuit of Fig. 18a

Fig. 19 - Clamped Inductive Load Test Circuit

Fig. 20 - Pulsed Collector Current Test Circuit